

## SGS5N150UF

### General Description

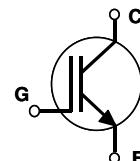
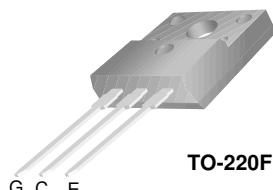
Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. SGS5N150UF is designed for the Switching Power Supply applications.

### Features

- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 4.7$  V @  $I_C = 5$  A
- High Input Impedance

### Application

Switching Power Supply - High Input Voltage Off-line Converter



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

| Symbol      | Description   | SGS5N150UF  | Units            |
|-------------|---|-------------|------------------|
| $V_{CES}$   | Collector-Emitter Voltage   | 1500        | V                |
| $V_{GES}$   | Gate-Emitter Voltage  | $\pm 20$    | V                |
| $I_C$       | Collector Current @ $T_C = 25^\circ\text{C}$                            | 10          | A                |
|             | Collector Current @ $T_C = 100^\circ\text{C}$                           | 5           | A                |
| $I_{CM(1)}$ | Pulsed Collector Current  | 20          | A                |
| $P_D$       | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$                    | 50          | W                |
|             | Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$                   | 20          | W                |
| $T_J$       | Operating Junction Temperature  | -55 to +150 | $^\circ\text{C}$ |
| $T_{stg}$   | Storage Temperature Range   | -55 to +150 | $^\circ\text{C}$ |
| $T_L$       | Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds | 300         | $^\circ\text{C}$ |

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

| Symbol          | Parameter                               | Typ. | Max. | Units                     |
|-----------------|---|------|------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case    | --   | 2.5  | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | --   | 62.5 | $^\circ\text{C}/\text{W}$ |

## Electrical Characteristics of IGBT

$T_C = 25^\circ\text{C}$  unless otherwise noted

| Symbol                             | Parameter                               | Test Conditions   | Min. | Typ. | Max.      | Units |
|------------------------------------|---|---|------|------|-----------|-------|
| <b>Off Characteristics</b>         |   |   |      |      |           |       |
| $\text{BV}_{\text{CES}}$           | Collector-Emitter Breakdown Voltage     | $\text{V}_{\text{GE}} = 0\text{V}$ , $\text{I}_C = 1\text{mA}$  | 1500 | --   | --        | V     |
| $\text{I}_{\text{CES}}$            | Collector Cut-Off Current               | $\text{V}_{\text{CE}} = \text{V}_{\text{CES}}$ , $\text{V}_{\text{GE}} = 0\text{V}$   | --   | --   | 1.0       | mA    |
| $\text{I}_{\text{GES}}$            | G-E Leakage Current                     | $\text{V}_{\text{GE}} = \text{V}_{\text{GES}}$ , $\text{V}_{\text{CE}} = 0\text{V}$   | --   | --   | $\pm 100$ | nA    |
| <b>On Characteristics</b>          |   |   |      |      |           |       |
| $\text{V}_{\text{GE}(\text{th})}$  | G-E Threshold Voltage                   | $\text{I}_C = 5\text{mA}$ , $\text{V}_{\text{CE}} = \text{V}_{\text{GE}}$   | 2.0  | 3.0  | 4.0       | V     |
| $\text{V}_{\text{CE}(\text{sat})}$ | Collector to Emitter Saturation Voltage | $\text{I}_C = 5\text{A}$ , $\text{V}_{\text{GE}} = 10\text{V}$  | --   | 4.7  | 5.5       | V     |
| <b>Dynamic Characteristics</b>     |   |   |      |      |           |       |
| $\text{C}_{\text{ies}}$            | Input Capacitance                       | $\text{V}_{\text{CE}} = 10\text{V}$ , $\text{V}_{\text{GE}} = 0\text{V}$ ,<br>$f = 1\text{MHz}$   | --   | 780  | --        | pF    |
| $\text{C}_{\text{oes}}$            | Output Capacitance                      |   | --   | 130  | --        | pF    |
| $\text{C}_{\text{res}}$            | Reverse Transfer Capacitance            |   | --   | 70   | --        | pF    |
| <b>Switching Characteristics</b>   |   |   |      |      |           |       |
| $t_{\text{d}(\text{on})}$          | Turn-On Delay Time                      | $\text{V}_{\text{CC}} = 600\text{ V}$<br>$\text{I}_C = 5\text{A}$<br>$\text{R}_G = 10\Omega$<br>$\text{V}_{\text{GE}} = 10\text{V}$<br>Inductive Load<br>$T_C = 25^\circ\text{C}$ | --   | 10   | --        | ns    |
| $t_r$                              | Rise Time                               |   | --   | 15   | --        | ns    |
| $t_{\text{d}(\text{off})}$         | Turn-Off Delay Time                     |   | --   | 30   | 50        | ns    |
| $t_f$                              | Fall Time                               |   | --   | 70   | 120       | ns    |
| $E_{\text{on}}$                    | Turn-On Switching Loss                  |   | --   | 190  | --        | uJ    |
| $E_{\text{off}}$                   | Turn-Off Switching Loss                 |   | --   | 100  | --        | uJ    |
| $E_{\text{ts}}$                    | Total Switching Loss                    |   | --   | 290  | 580       | uJ    |
| $Q_g$                              | Total Gate Charge                       |   | --   | 30   | 45        | nC    |
| $Q_{\text{ge}}$                    | Gate-Emitter Charge                     | $\text{V}_{\text{CE}} = 600\text{ V}$ , $\text{I}_C = 5\text{A}$<br>$\text{V}_{\text{GE}} = 10\text{V}$   | --   | 3    | 5         | nC    |
| $Q_{\text{gc}}$                    | Gate-Collector Charge                   |   | --   | 15   | 25        | nC    |

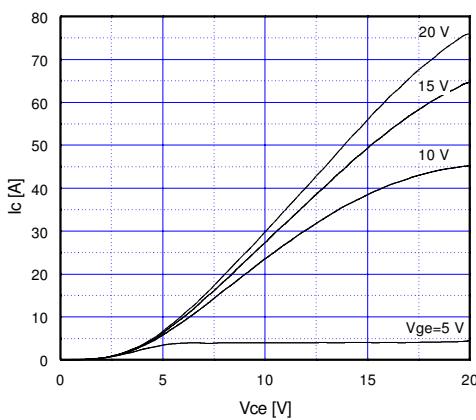


Fig 1. Typical Output Characteristics

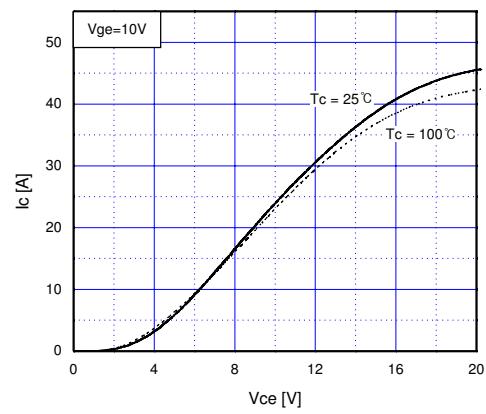


Fig 2. Typical Output Characteristics

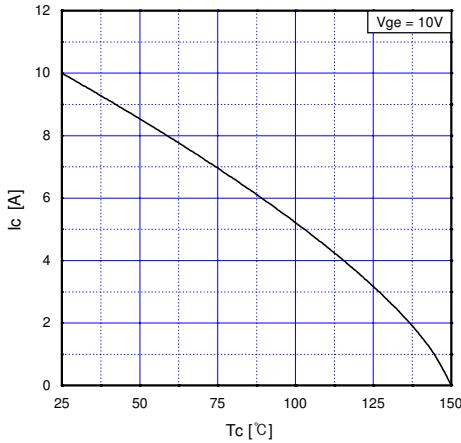


Fig 3. Maximum Collector Current vs. Case Temperature

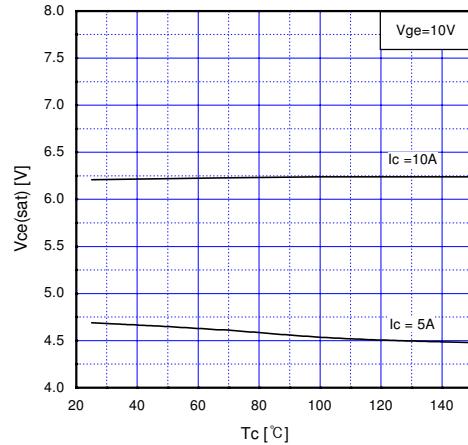


Fig 4. Saturation Voltage vs. Case Temperature

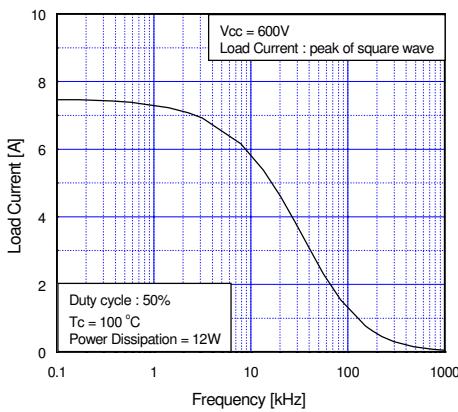


Fig 5. Load Current vs. Frequency

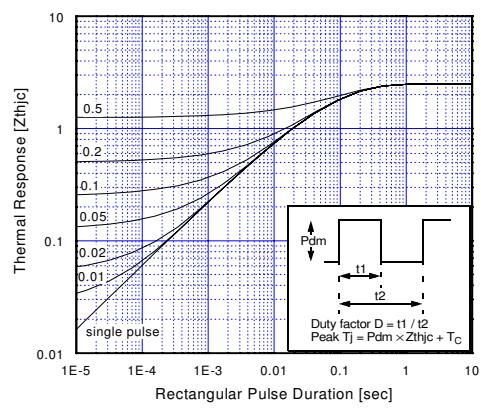
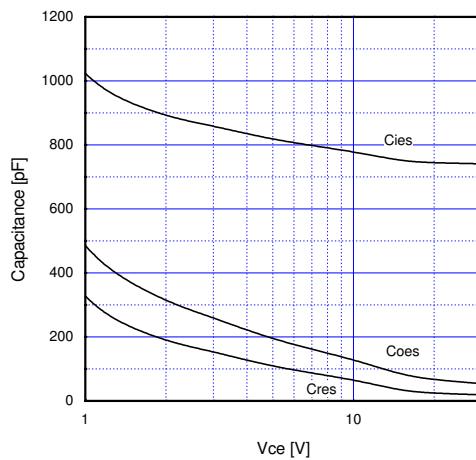
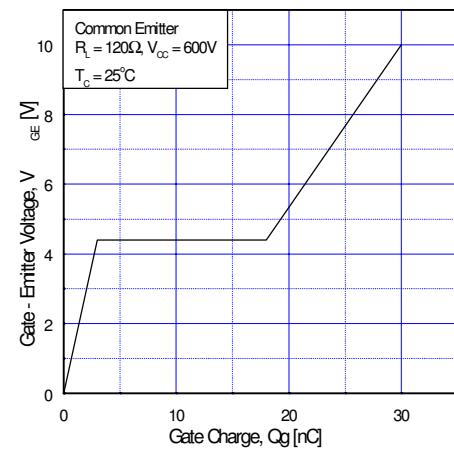


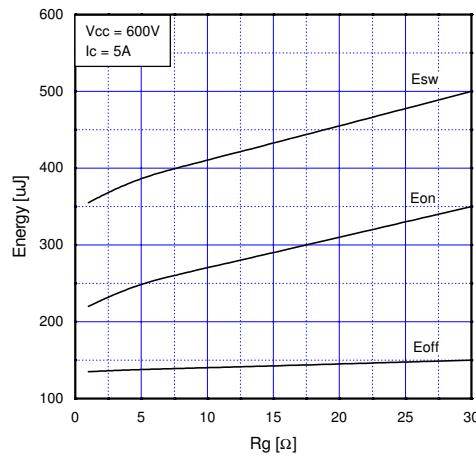
Fig 6. Transient Thermal Impedance of IGBT Junction to Case



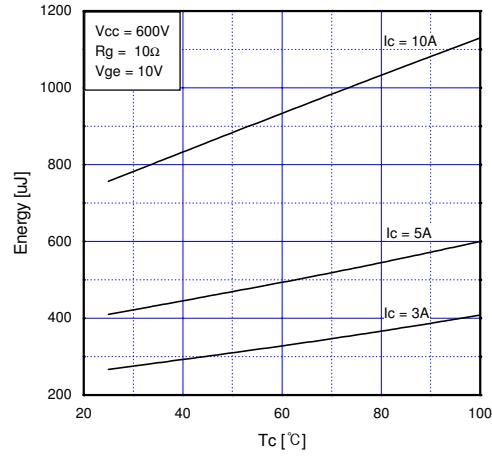
**Fig 7. Typical Capacitance vs.  
Collector to Emitter Voltage**



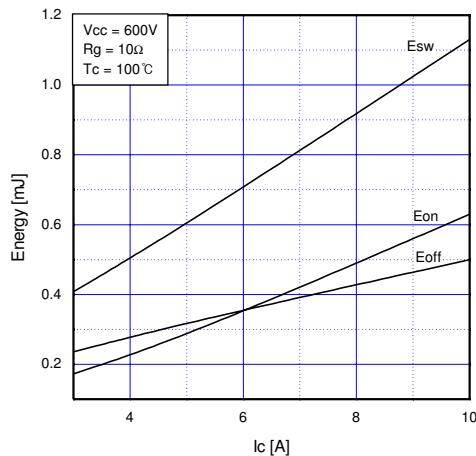
**Fig 8. Typical Gate Charge Characteristic**



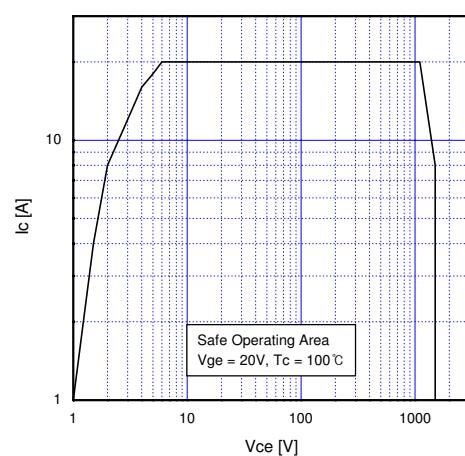
**Fig 9. Typical Switching Loss vs.  
Gate Resistance**



**Fig 10. Typical Switching Loss vs.  
Case Temperature**



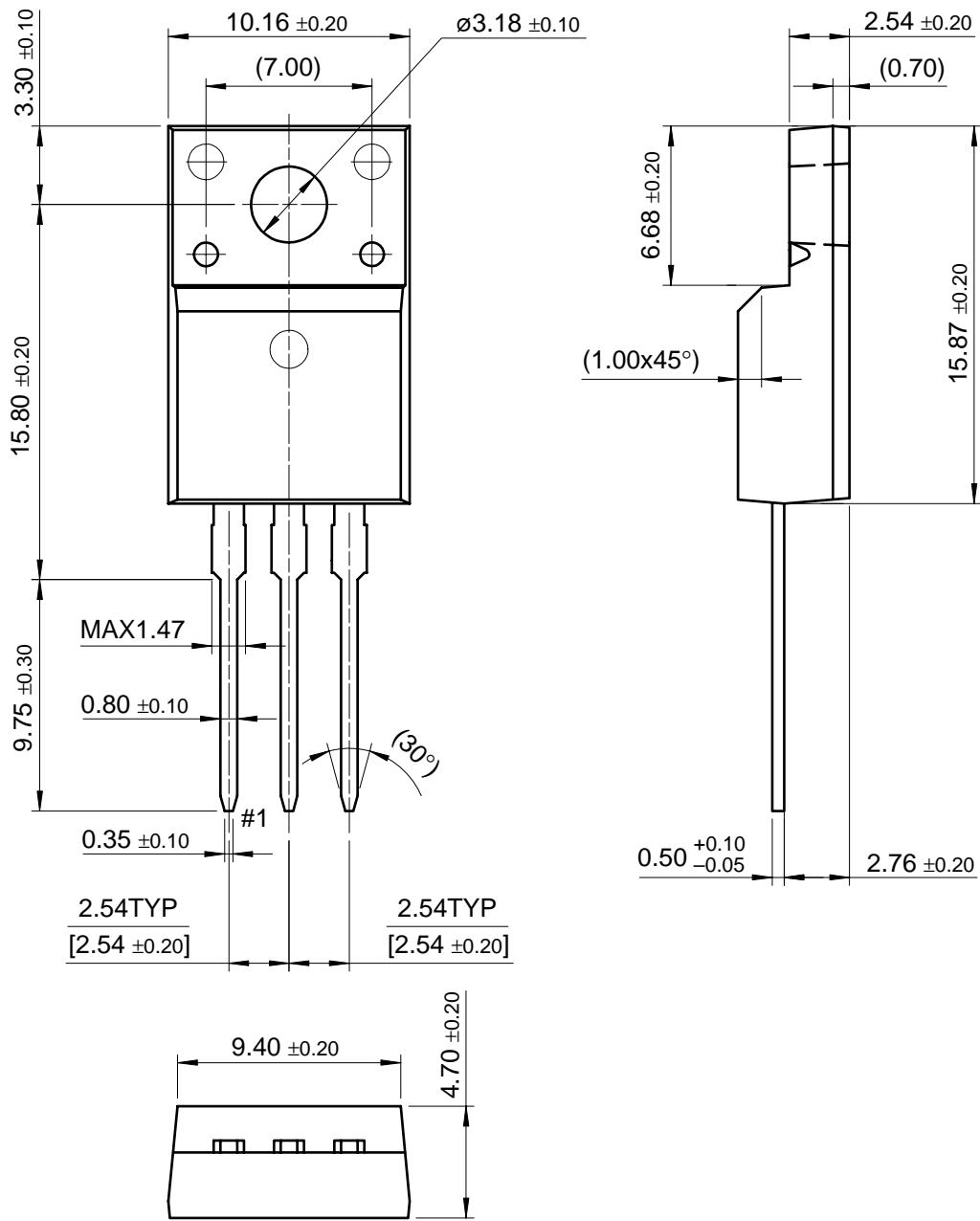
**Fig 11. Typical Switching Loss vs.  
Collector Current**



**Fig 12. Turn-Off SOA**

## Package Dimension

## TO-220F (FS PKG CODE AQ)



Dimensions in Millimeters

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